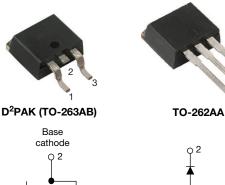
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VS-MURB820HM3, VS-MURB820-1HM3

Vishay Semiconductors

Ultrafast Rectifier, 8 A FRED Pt®

2



01 03 N/C Anode

VS-MURB820HM3

↓ ↓ 3 N/C Anode VS-MURB820-1HM3

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS								
I _{F(AV)}	8 A							
V _R	200 V							
V _F at I _F	0.75 V							
t _{rr}	35 ns							
T _J max.	175 °C							
Package	D ² PAK (TO-263AB), TO-262AA							
Circuit configuration	Single							

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD-201 class 1A thin whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: D²PAK (TO-263AB), TO-262AA Molding compound meets UL 94 V-0 flammability rating Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS					
Peak repetitive reverse voltage	V _{RRM}		200	V					
Average rectified forward current	I _{F(AV)}	Total device, rated V _R , T _C = 150 °C	8						
Non-repetitive peak surge current	I _{FSM}		100	А					
Peak repetitive forward current	I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 150 °C	16						
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C					

ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-				
Forward voltage	V _F	I _F = 8 A	-	0.92	0.975	V			
		I _F = 8 A, T _J = 150 °C	-	0.75	0.895				
Reverse leakage current		$V_{R} = V_{R}$ rated	-	-	5	μA			
Reverse leakage current	IR	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	μΑ			
Junction capacitance	CT	V _R = 200 V	-	25	-	pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH			

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Document Number: 95902

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COMPLIANT

HALOGEN

FREE



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 50$	A/ μ s, V _R = 30 V	-	-	35				
	+	I _F = 0.5 A, I _R = 1.0 A,	-	-	25					
	t _{rr}	T _J = 25 °C		-	20	-	A nC			
		T _J = 125 °C	$I_F = 8 A$	-	34	-				
Deck receiver / current	I _{RRM}	T _J = 25 °C		-	1.7	-				
Peak recovery current		T _J = 125 °C	dl _F /dt = 200 A/µs V _B = 160 V	-	4.2	-				
Reverse recovery charge	Q _{rr}	T _J = 25 °C	VR - 100 V	-	23	-				
		T _J = 125 °C		-	75	-	10			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	3.0					
Thermal resistance, junction to ambient	R _{thJA}		-	-	50	°C/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-					
Weight			-	2.0	-	g				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking davias		Case style D ² PAK (TO-263AB)	MURB820H							
Marking device		Case style TO-262AA		MURB	820-1H					

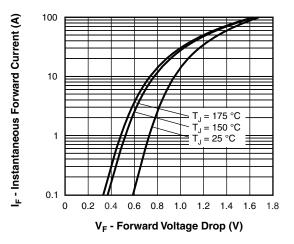


Fig. 1 - Typical Forward Voltage Drop Characteristics

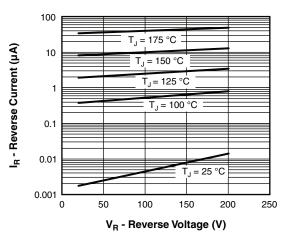


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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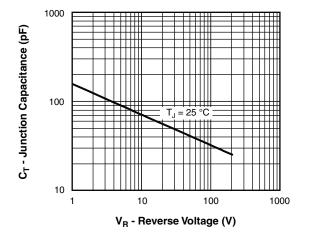


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

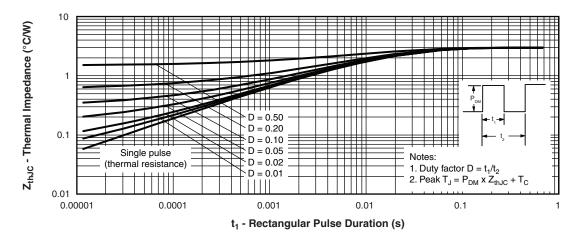
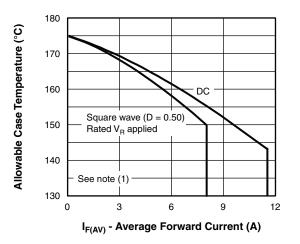
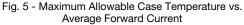


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R}1} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R}1} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \\ \end{array}$

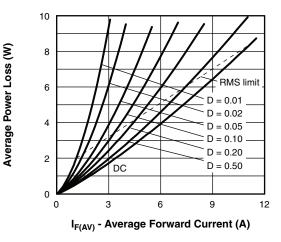


Fig. 6 - Forward Power Loss Characteristics

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VS-MURB820HM3, VS-MURB820-1HM3





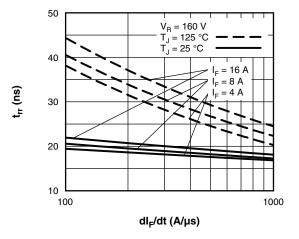


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

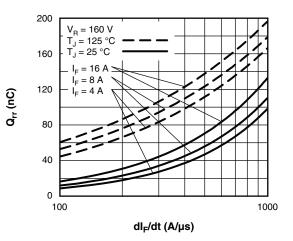


Fig. 8 - Typical Stored Charge vs. dl_F/dt

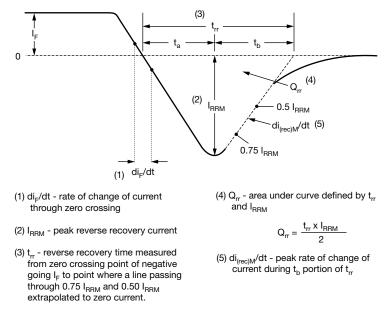
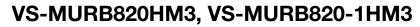


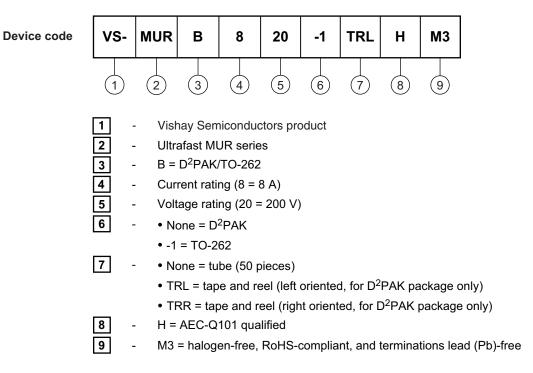
Fig. 9 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE



ORDERING INFORMATION									
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION							
VS-MURB820HM3	50	Antistatic plastic tube							
VS-MURB820TRRHM3	800	13" diameter reel							
VS-MURB820TRLHM3	800	13" diameter reel							
VS-MURB820-1HM3	50	Antistatic plastic tube							

LINKS TO RELATED DOCUMENTS		
Dimensions	D ² PAK (TO-263AB)	www.vishay.com/doc?95046
Dimensions	TO-262AA	www.vishay.com/doc?95419
Part marking information	D ² PAK (TO-263AB)	www.vishay.com/doc?95444
	TO-262AA	www.vishay.com/doc?95443
Packaging information		www.vishay.com/doc?95032
SPICE model		www.vishay.com/doc?96995

Outline Dimensions



D²PAK

DIMENSIONS in millimeters and inches

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SHA



SYMBOL	MILLIMETERS		INC	INCHES		NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 08-Jul-15

1

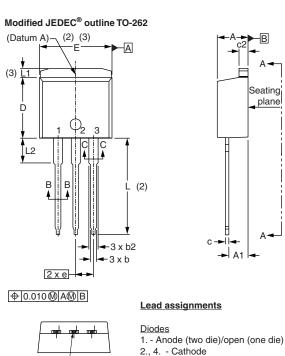
Outline Dimensions



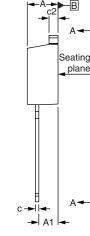
Vishay Semiconductors

TO-262

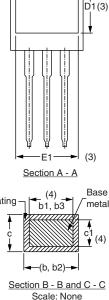
DIMENSIONS in millimeters and inches



Lead tip -



E1 Plating



Е

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. А 4.06 4.83 0.160 0.190 2.03 A1 3.02 0.080 0.119 b 0.51 0.99 0.020 0.039 b1 0.51 0.89 0.020 0.035 4 b2 1.14 1.78 0.045 0.070 1.14 1.73 0.045 0.068 4 b3 0.38 0.74 0.015 0.029 С 0.38 0.58 0.015 0.023 4 c1 1.14 1.65 0.045 0.065 c2 D 8.51 9.65 0.335 0.380 2 D1 6.86 8.00 0.270 0.315 3 Е 9.65 10.67 0.380 0.420 2, 3 E1 7.90 8.80 0.311 0.346 3 0.100 BSC 2.54 BSC е L 13.46 14.10 0.530 0.555 L1 _ 1.65 0.065 3 _ 3.36 0.132 0.146 L2 3.71

3. - Anode

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Controlling dimension: inches

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

Outline conform to JEDEC TO-262 except A1 (maximum), (6) b (minimum), D1 (minimum) and L2 where dimensions derived the actual package outline

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Document Number: 95419

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